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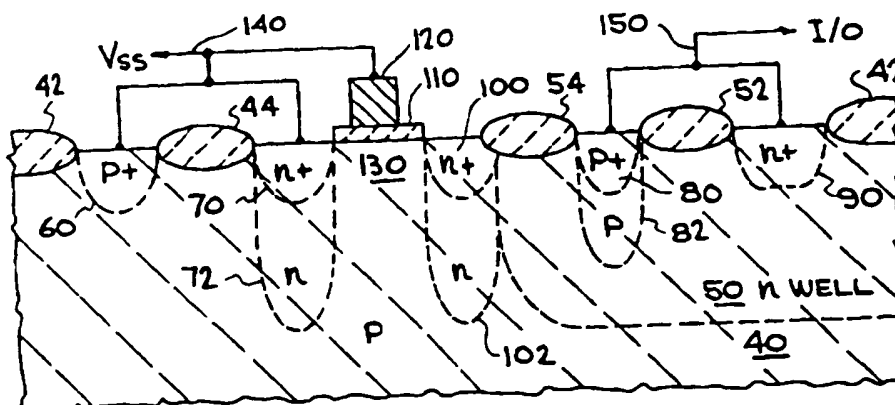
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(54) Title: METHOD FOR FORMING MINIMUM AREA STRUCTURES FOR SUB-MICRON CMOS ESD PROTECTION IN INTEGRATED CIRCUIT STRUCTURES WITHOUT EXTRA IMPLANT AND MASK STEPS, AND ARTICLES FORMED THEREBY



(57) Abstract

A method and resulting structure is disclosed for extending or enlarging the effective volumes of one or more source, drain, and/or emitter regions of integrated circuit structures such as an SCR structure and/or an MOS structure designed to protect an integrated circuit structure from damage due to electrostatic discharge (ESD). The additional effective volume allows the SCR and/or MOS protection devices to handle additional energy from an electrostatic discharge applied, for example, to I/O contacts electrically connected to the SCR protection structure. The additional effective volume is obtained, without additional doping or masking steps, by forming individual deep doped regions or wells, beneath one or more heavily doped source, drain, and emitter regions, at the same time and to the same depth and doping concentration as conventional main P wells and/or N wells which are simultaneously formed in the substrate, whereby no additional masks and implanting steps are needed.

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METHOD FOR FORMING MINIMUM AREA STRUCTURES  
FOR SUB-MICRON CMOS ESD PROTECTION IN  
INTEGRATED CIRCUIT STRUCTURES WITHOUT EXTRA IMPLANT  
AND MASK STEPS, AND ARTICLES FORMED THEREBY

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BACKGROUND OF THE INVENTION

1. Field of the Invention

This invention relates to provision of electrostatic discharge (ESD) protection for CMOS semiconductor devices in integrated circuit structures. More particularly, in one embodiment this invention relates to provision of electrostatic discharge protection for CMOS semiconductor devices using an SCR structure formed in a minimum area without using an additional implant and mask to provide ESD protection; and in another embodiment, the invention comprises improvements in the buffer portion of the integrated circuit structure to provide the ESD protection without the use of the SCR structure.

2. Description of the Related Art

It is important to prevent damage to gate oxides at input buffers and to NMOS components at bidirectional buffers and output drivers caused by electrostatic discharge (ESD). To prevent such damage, an on-chip ESD protection structure must be triggerable and release a built-up charge at a voltage substantially below the breakdown voltages for the gate oxides and NMOS components.

Some prior art structures have been proposed to provide ESD protection. However, at least in some cases, such protective circuitry require the low voltage triggering of structures which include a parasitic lateral NPN transistor and a linked parasitic vertical PNP transistor. However, this can also cause voltage latchup to occur in the CMOS structure being protected against ESD damage. Such voltage latchup is unacceptable and alternate means for providing ESD protection have, therefore, been explored.

In a related application entitled "ESD PROTECTION FOR DEEP SUBMICRON CMOS DEVICES WITH MINIMUM TRADEOFF FOR LATCHUP BEHAVIOUR", previously filed

by one of us on November 13, 1995, as United States Patent Application Serial No. 08/556,599, assigned to the assignee of this invention, and the disclosure of which is hereby incorporated by reference herein, an SCR structure was disclosed and claimed to provide ESD protection. This structure is generally shown in Figure 1. This structure provides a tunable  
5 low voltage-triggering SCR in which triggering occurs at voltages in the range of 5-20 volts.

In the structure of the aforementioned Serial No. 08/556,599, as shown in Figure 1, a P doped substrate 2 is provided with a P+ contact region 4 which provides an electrical contact to substrate 2. An N+ source region 6, also formed in substrate 2, is separated from P+ contact region 4 by a first field oxide region 8. N+ source region 6 comprises the source  
10 for the MOSFET of the SCR structure which provides the ESD protection. An N well 10 is also provided in substrate 2 and has a P+ emitter region 12 formed therein as well as an N+ contact region 14 formed therein, with N+ contact region 14 serving as an electrical contact to main N well 10. P+ emitter region 12 and N+ contact region 14 are separated from one another by a second field oxide region 16. At the edge of main N well 10 and shown in  
15 physical and electrical contact with main N well 10 is an N+ floating drain region 18 which serves as the drain for the MOSFET of the SCR structure. Floating drain region 18 further serves as the base of the lateral parasitic PNP bipolar transistor. N+ floating drain region 18 is separated from P+ emitter region 12 by a third field oxide region 20.

In the illustrated embodiment, a gate oxide layer 22 is formed on the surface of substrate 2  
20 between N+ source contact region 6 and N+ floating drain region 18, with a polysilicon gate electrode 24 formed over gate oxide 22. A channel region 26 lies in substrate 2 beneath gate oxide layer 22.

P+ contact region 4, N+ source region 6, and gate electrode 24 are electrically connected together by a first electrically conductive bus member 28 which is, in turn, electrically  
25 connected to ground, e.g., a Vss bus. First electrically conductive member 28 may comprise one or more doped polysilicon layers or one or more metal layers, or a combination thereof as is well known to those skilled in the art of forming electrical busses for integrated circuit structures. P+ emitter region 12 and N+ contact region 14 are electrically connected together

by a second electrically conductive bus member 30 to a portion of the integrated circuit structure to be protected against damage by ESD, such as for example, an input/output (I/O) pin.

5 The structure disclosed and claimed in Serial No. 08/556,599, and the process of making same, includes the use of retrograde well fabrication or conventional well implant and epitaxial methods to form the different P well and N well regions; replacement of a field oxide with a thinner gate oxide region under a polysilicon MOSFET gate region; connection of the polysilicon MOSFET gate region to a grounded electrode rather than to the I/O electrode; use of buffered contacts rather than the prior art use of unbuffered contacts; achievement of  
10 relatively low dynamic or differential resistance in the on-state, which reduces the associated ESD resistance; use of a thin guard band that is integrated with one of the tap regions to suppress minority carrier injection and to control development of latchup due to SCR electrode injection during latchup testing and subsequent operation; and recognition and treatment of the role of development and triggering of lateral and vertical bipolar transistor action in promoting  
15 or initiating ESD in an SCR.

In this regard, it should be noted that in providing ESD protection for submicron integrated circuit devices, a low triggering voltage and low associated resistance for the ESD triggering device are both desired. However, these desired features are often inconsistent with desired core performance characteristics where high triggering voltage of parasitic bipolar devices is  
20 built in to suppress development of latchup in the device. The ESD protective device described and claimed in the aforementioned patent application Serial No. 08/556,599, provides good ESD protection without, however, sacrificing latchup protection.

While the structure and method proposed in the aforementioned patent application Serial No. 08/556,599, has provided satisfactory protection against ESD without sacrificing latchup  
25 protection, the structure shown in Figure 1 is limited in the size required to dissipate the energy or power from an electrostatic discharge of 2 kV from a human body (a human body model or HBM zapping). As seen in Figure 1, the length of the circuitry required to provide the desired ESD protection is fixed by the devices themselves. In order to provide sufficient dissipation of such a 2 kV HBM zapping, i.e., in order to be large enough to handle the

energy or power from a 2 kV HBM zapping (for average junction depths of 0.2 micrometers ( $\mu\text{m}$ ) or less), the width of the circuitry (the direction into the paper in Figure 1) would have to be at least about 2.5 mils (about  $63.5 \mu\text{m}$ ). However, the requirements for smaller sizes with shrinking dimensions of the integrated circuits structures make this size unacceptable for certain applications. It would, therefore, be desirable to provide the circuitry of the  
5      aforementioned patent application Serial No. 08/556,599, constructed in such a way as to occupy a smaller area of the substrate on which the ESD protection structure of the integrated circuit structure is formed.

### SUMMARY OF THE INVENTION

10      The invention provides a method and resulting structures for extending or enlarging the effective volumes of one or more source, drain, and/or emitter regions of integrated circuit structures such as an SCR structure and/or an MOS structure designed to protect an integrated circuit structure from damage due to electrostatic discharge (ESD). The additional effective  
15      volume allows the SCR and/or MOS protection devices to handle additional energy from an electrostatic discharge applied, for example, to I/O contacts electrically connected to the SCR protection structure. The additional effective volume is obtained, without additional doping or masking steps, by forming deep doped regions or wells, beneath one or more heavily doped source, drain, and emitter regions, at the same time and to the same depth and doping concentration as conventional P wells and/or N wells which are simultaneously formed in the  
20      substrate, whereby no additional masks and implanting steps are needed.

### BRIEF DESCRIPTION OF THE DRAWINGS

Figure 1 is a fragmentary vertical side section view of the ESD protection device described and claimed in Serial No. 08/556,599.

25      Figure 2 is a top view showing the area on a semiconductor substrate occupied by a preferred embodiment of the ESD protection structure of the invention, showing the dimension defined as length and the dimension defined as width in the area of the ESD protection structure.

Figure 3 is a fragmentary vertical side section view of the ESD protection structure of the invention, taken along lines III-III of Figure 2, showing a preferred embodiment of the ESD protection structure of the invention along its length.

Figure 4 is a schematic view of the electrical circuitry defined by the ESD protection structure  
5 shown in Figure 3.

Figures 5-11 are fragmentary vertical cross-sectional views of alternate embodiments to the structure shown in Figures 2 and 3, illustrating the various structural ways in which the overall effective volume of the source, drain, and/or emitter regions of the ESD protection structure may be increased to thereby increase the total amount of energy which can be absorbed and  
10 dissipated by the ESD protection structure while either maintaining the same width in the area of the substrate occupied by the ESD protection structure or while reducing the width dimension of the area.

Figure 12 is a fragmentary vertical cross-sectional view showing an initial stage of construction of the ESD protection structure of the invention showing formation of the main N well and the  
15 simultaneous formation of the small N wells of the same depth which are associated with the N+ source and drain regions of the MOSFET device of the SCR structure, as well as a small P well beneath the P+ emitter, to extend the respective effective volumes of the N+ source and drain regions and the P+ emitter region to thereby increase the overall volume of the ESD protection structure of the invention.

20 Figure 13 is a fragmentary vertical cross-sectional view showing the masking of the active regions of the substrate while field oxide is grown to provide electrical isolation between the respective active regions.

Figure 14 is a fragmentary vertical cross-sectional view showing formation of the gate oxide and overlying gate electrode for the MOSFET device of the SCR structure of the invention.

Figure 15 is a fragmentary vertical cross-sectional view showing the N+ implantation of active regions of the substrate to form the N+ source, N+ drain and N+ contact for the N well, while other active regions are masked off.

5 Figure 16 is a fragmentary vertical cross-sectional view showing the P+ implantation of other active regions of the substrate where the P+ emitter and the P+ contact to the P substrate are formed, while other regions are masked off.

Figure 17 shows, in diagram form, the relationship of the I/O pad, the SCR structure (which comprises the primary ESD protection structure) the ESD resistor, and the output buffer and/or input receiver section for the N drivers and P drivers which provides secondary ESD  
10 protection for the remainder of the integrated circuit structure.

Figure 18 is a schematic view of the electrical circuitry defined by an output driver for an output buffer located between the ESD resistor and the remainder of the integrated circuit structure.

15 Figure 19 is a schematic view of the electrical circuitry defined by an input receiver structure located between the ESD resistor and the remainder of the integrated circuit structure.

Figure 20 is a fragmentary vertical side section view of the of the ESD diode structure of the input receiver of Figure 19, showing the individual N wells and P wells formed below the respective P+ and N+ regions in accordance with the invention.

20 Figure 21 is a fragmentary vertical side section view illustrating a preferred method of forming the structure shown in Figure 20 wherein no additional processing steps or masks are utilized.



## DETAILED DESCRIPTION OF THE INVENTION

### a. Description of the Preferred Embodiment of the Structure

Figures 2-4 illustrate a structure designed in accordance with the invention to protect an integrated circuit structure on a semiconductor substrate against damage from ESD. The ESD protection structure comprises an SCR structure having one or more source, drain, and/or emitter regions effectively increased in volume to permit the SCR structure to handle additional energy from an electrostatic discharge, i.e., increasing the ESD energy which the ESD protection structure is capable of absorbing, without, however, increasing the width of the SCR structure.

10 Alternatively, the ESD protective structure is capable of handling the same amount of energy as the structure shown in Figure 1, but with reduced width, due to the added depth of the active regions which can provide the same effective volume, but with reduced width. In this regard, it should be noted that the distribution of the volume of the active source, drain, and emitter regions of the SCR protective structure more evenly across all three dimensions (width, 15 length, and depth) may provide enhanced peak protection against ESD.

When the area of the substrate taken occupied by the ESD protection structure is to be reduced, it must be reduced in the width direction rather than the length, as indicated in Figure 1, since any substantial changes in the length could change the SCR triggering voltage. As used herein with respect to the area occupied by the ESD protection structure, the term 20 "length" is intended to define the direction of current flow in the SCR structure, i.e., the direction in which the channel length of the MOSFET device of the SCR structure is measured, while the term "width" is intended to define the space occupied by the SCR structure in the channel width direction of the MOSFET, i.e., perpendicular to the current flow.

25 For purposes of this application, an increase in volume of the SCR protection structure of the invention is intended to mean an increase in volume based on an increase in the effective depth

of one or more of the source, drain, and/or emitter regions of the SCR structures in the ESD protection structure regardless of the any reduction in width of the SCR structure.

The use of the terms "individual N well" or "individual P well" is intended to define an N well or P well which is contiguous and in electrical contact with an individual P+ or N+ active region in the semiconductor substrate; while the terms "main N well" or "main P well" are intended to define a well of opposite conductivity to the substrate and formed in the substrate to permit the formation in such main well of a plurality of active regions of opposite conductivity type to the conductivity type of the main well.

Referring now in particular to Figures 2 and 3, a portion of a P doped semiconductor substrate 40 is shown in which the SCR structure of the invention will be constructed to provide the desired ESD protection. As particularly shown in Figure 2, the active region of substrate 40 in which the SCR structure will be constructed is shown surrounded by field oxide 42. Substrate 40 has a main N well 50 formed therein using either a retrograde well implant process or a conventional well implant process. While the illustrated embodiment shows no P well because the P doped semiconductor substrate 40 is either blanket deposited or initially formed to form a P well of the entire substrate, it will be appreciated that a separate P well could also be formed, particularly if the substrate is either intrinsic or only lightly P doped.

Substrate 40 is provided with a P+ contact region 60 which provides an electrical contact to P doped substrate 40 (or to a P well when a P well is used). An N+ source region 70 is also shown formed in substrate 40 and separated from P+ contact region 60 by a second field oxide region 44. In the illustrated embodiment shown in Figure 2, a source N well region 72 is shown formed below N+ source region 70, in accordance with the invention. Source N well region 72 has a depth equal to the depth of main N well 50, which, in accordance with the invention, enables both N wells to be simultaneously formed using the same masking and implantation steps, as will be discussed below. Source N well region 72 serves to extend the overall effective volume of N+ source region 70 of the SCR used in the ESD protection structure to enable the ESD protection structure to dissipate an increased amount of energy from the ESD. As will be discussed below, the exact shape and location of the source N well region associated with N+ source region 70 may vary, so long as it remains in physical and

electrical contact with N+ source region 70, and its depth remains the same as main N well 50.

First P+ contact region 60 and N+ source region 70 preferably each have a length (as measured from left to right in the dimension illustrated in Figure 3) of from about 1  $\mu\text{m}$  (10,000 Angstroms ( $\text{\AA}$ )) to about 9  $\mu\text{m}$  (90,000  $\text{\AA}$ ), a width (the dimension into the paper in Figure 3) of from about 1 mil (25.4  $\mu\text{m}$ ) to about 2.5 mils (63.5  $\mu\text{m}$ ), and a depth (height) of from about 0.1  $\mu\text{m}$  (1,000  $\text{\AA}$ ) to about 0.2  $\mu\text{m}$  (2,000  $\text{\AA}$ ). First P+ contact region 60 and N+ source contact region 70 preferably each have a carrier concentration of from about  $10^{19}$  to about  $10^{21}$  atoms/cm<sup>3</sup>.

10 Field oxide region 44, separating P+ contact region 60 and N+ source region 70, has a thickness (depth) preferably ranging from about 20 nanometers (20 nm or 200  $\text{\AA}$ ) to about 600 nm (6000  $\text{\AA}$ ), and a length (distance between first P+ contact region 60 and N+ source region 70) of from about 0.1  $\mu\text{m}$  (100 nm or 1,000  $\text{\AA}$ ) to about 10  $\mu\text{m}$  (10,000 nm or 100,000  $\text{\AA}$ ).

A P+ emitter region 80 and a N+ contact region 90 are formed in main N well 50, with N+ contact region 90 serving as an electrical contact to main N well 50. P+ emitter region 80 and N+ contact region 90 preferably each have a carrier concentration of from about  $10^{20}$  to about  $10^{21}$  atoms/cm<sup>3</sup>. P+ emitter region 80 and N+ contact region 90 are separated by a third field oxide region 52 which also has a thickness (depth) ranging from about 20 nm (200  $\text{\AA}$ ) to about 600 nm (6000  $\text{\AA}$ ), and a length (distance between second P+ contact region 80 and second N+ contact region 90) of from about 0.1  $\mu\text{m}$  (100 nm or 1,000  $\text{\AA}$ ) to about 10  $\mu\text{m}$  (10,000 nm or 100,000  $\text{\AA}$ ). Formed below P+ emitter region 80 is a P well 82 which is preferably formed at the same time as N wells 72 and 102 and main N well 50, although not to the same depth (to prevent shorting of P well 82 to P substrate 40), as will be discussed below.

25 Adjacent the edge of main N well 50 is an N+ floating drain region 100 which serves as the drain for the MOSFET device of the SCR structure, but also as the base of a lateral parasitic PNP bipolar transistor as well as the base of a vertical PNP transistor, as will be discussed below with respect to Figure 4. N+ floating drain region 100 preferably has a carrier

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concentration of from about  $10^{19}$  to about  $10^{20}$  atoms/cm<sup>3</sup>. N+ floating drain region 100 is separated from second P+ contact region 80 by a fourth field oxide region 54. Formed below N+ floating drain region 100 is an N well 102 which, like N well 72, is formed to a depth equal to the depth of main N well 50. N well 102 is formed at the same time as main N well 50 and N well 72, as will be discussed below.

P+ emitter region 80, N+ contact region 90, and N+ floating drain region 100 each preferably have dimensions similar to P+ contact region 60 and N+ source region 70, i.e., a length (as measured from left to right in the dimension illustrated in Figure 3) of from about 1  $\mu\text{m}$  (10,000 Angstroms ( $\text{\AA}$ )) to about 9  $\mu\text{m}$  (90,000  $\text{\AA}$ ), a width (the dimension into the paper in Figure 3) of from about 1 mil (25.4  $\mu\text{m}$ ) to about 2.5 mils (63.5  $\mu\text{m}$ ), and a depth (height) of from about 0.1  $\mu\text{m}$  (1,000  $\text{\AA}$ ) to about 0.2  $\mu\text{m}$  (2,000  $\text{\AA}$ ).

In the illustrated embodiment, a gate oxide layer 110 is formed on the surface of substrate 40 between N+ source region 70 and N+ floating drain region 100, with a gate electrode 120, preferably comprising doped polysilicon, formed over gate oxide 110. Gate oxide layer 110 preferably has a thickness ranging from about 7 nm (70  $\text{\AA}$ ) to about 10 nm (100  $\text{\AA}$ ), typically about 7 nm. A channel region 130 in substrate 40 beneath gate oxide layer 110 has a channel length of from about 0.1  $\mu\text{m}$  (1,000  $\text{\AA}$ ) to about 1  $\mu\text{m}$  (10,000  $\text{\AA}$ ).

P+ contact region 60, N+ source region 70, and gate electrode 120 are electrically connected together by a first electrically conductive bus member 140 which is, in turn, electrically connected to ground, e.g., a Vss bus. First electrically conductive bus member 140 may comprise one or more doped polysilicon layers or one or more metal layers, or a combination thereof as is well known to those skilled in the art of forming electrical busses for integrated circuit structures.

P+ emitter region 80 and N+ contact region 90 are electrically connected together by a second electrically conductive bus member 150 to a portion of the integrated circuit structure to be protected against damage by ESD, such as for example, an input/output (I/O) pin.

Figure 4 illustrates an electrical schematic of the ESD protection device comprising the SCR and the associated lateral and vertical parasitic bipolar transistors and resistances previously shown in Figure 3 to provide ESD protection to portions of an integrated circuit structure such as the I/O buffer circuits. Resistors R1 and R2 each represent resistances through substrate 40 (R2 could represent the resistance through a P well, if P+ contact region 60, N+ source region 70, and drain region 100 were formed in a P well instead of a P type substrate), while resistance R3 represents the resistance through main N well 50. Node points N1, N2, and N3 respectively correspond to first P+ contact region 60, N+ source region 70, and gate electrode 120 in Figure 3, while nodes N4 and N5 respectively correspond to P+ emitter region 80 and N+ contact region 90 in Figure 3. MOSFET transistor T1 in Figure 4 corresponds to source region 70, gate oxide layer 110, gate electrode 120, and floating drain region 100 in Figure 3. Lateral transistors T2 and T3 in Figure 4 comprises the parasitic bipolar transistors formed between emitter region 80, P+ contact 60 (which serves as the collector for transistors T2 and T3), and floating drain region 100 (which serves as the base for transistors T2 and T3) in Figure 3.

It will be noted that in contrast to the ESD protection structure described and claimed in aforementioned copending application Serial No. 08/556,599, the effective volume of N+ source region 70, N+ floating drain region 100, and P+ emitter region 80 have, respectively, been enlarged by the respective provision of source N well region 72, floating drain N well region 102, and P well region 82 which respectively extend below N+ source contact region 70, N+ floating drain region 100, and emitter region 80, with N wells 72 and 102 extending down to the same depth in substrate 40 as main N well 50, i.e., about  $1\text{ }\mu\text{m}$  ( $\sim 10,000\text{ }\text{\AA}$ ), while P well 82 extends down about  $0.8\text{ }\mu\text{m}$  ( $\sim 8,000\text{ }\text{\AA}$ ).

It should also be noted that while an increase in the effective respective volumes of N+ source region 70, N+ floating drain region 100, and P+ emitter region 80 have all been shown together, an increase in the amount of energy which may be dissipated, over the structure described and claimed in the aforementioned Serial No. 08/556,599, may be obtained by extending the volume of any one or two of the source, drain, or emitter regions. However, since the extension of the effective volume of all of the source, drain, and emitter regions may be obtained, in accordance with the invention, without the need for additional processing steps

or masks, as will be described below, it is preferable to extend the effective volume of all three active regions of the SCR structure together.

b. Description of Alternate Embodiments of the Structures

With respect to the exact shape of the N wells or P well, and their respective relationships to the disposition and shape of the N+ or P+ active regions, a number of different geometries may be effectively used. Referring now to Figures 5-11, other embodiments are shown comprising modifications of either the extended drain N well region 102 (Figures 5-7) or the extended source N well region 72 (Figures 8-11). Furthermore, the geometries illustrated in Figures 8-11 for modifications of N well region 70 may also be employed for modifications to P well 82 as well.

Referring now to Figure 5, the effective volume of N+ floating drain region 100 has been increased by forming N well 102' adjacent N+ floating drain region 100 and under field oxide 54, rather than beneath N+ floating drain region 100 as in the previous embodiment shown in Figure 3. It should be noted that N well 102' is positioned to be contiguous and in electrical contact with both main N well 50 and N+ floating drain region 100.

In Figure 6, another variation of the increase in the effective volume of N+ floating drain region 100 is illustrated wherein an additional field oxide region 56 is formed between N+ floating drain region 100 and gate oxide 110 and an N well 102'' is formed beneath field oxide region 56 which is contiguous, and in contact electrically, with N+ floating drain region 100 to thereby effectively extend the volume of N+ floating drain region 100.

Figure 7 shows another variation which also adds a field oxide region 56, but which also creates a second floating drain region 100' between field oxide regions 54 and 56. In this instance, an N well 103 is formed beneath field oxide region 56 which is contiguous with and electrically connected to both floating drain region 100 and floating drain region 100', thereby extending the effective volume of the floating drain region.

It should be further noted that the effective length of the N+ floating drain region spacing (between gate oxide 110 and N well 50) should preferably remain substantially the same in all of the embodiments respectively shown in Figures 3, 5, 6, and 7, so that the electrical characteristics of the SCR structure do not change.

- 5 Turning now to Figures 8-11, other embodiments are illustrated which show different geometries for the N well(s) providing the increase in the effective volume of N+ source region 70. In Figure 8, an N well 172 is shown formed beneath field oxide 44. N well 172, like N well 72 of the embodiment shown in Figure 3, is contiguous and in electrical contact with N+ source region 70. Figure 9 shows another embodiment wherein an additional field  
10 oxide region 144 is formed between N+ source region 170 and gate oxide 110, and N well 172' is then formed beneath field oxide region 144. Again, N well 172', like N wells 72 and 172, is contiguous and in electrical contact with the adjoining N+ source region (in this case N+ source region 170) to thereby provide the desired increase in effective volume of the N+ source region in substrate 40, in accordance with the invention.
- 15 Figure 10 shows yet another embodiment in which an additional field oxide region 210 is formed with an N well 220 formed beneath field oxide 210. In this embodiment, two N+ source regions, 214 and 218, are formed, respectively, on each side of field oxide 210 with N+ source regions 214 and 218 both contiguous and in electrical communication with N well 220 to increase the effective volume of the combined N+ source region. In the  
20 embodiment of Figure 11, a second field oxide region 230 is formed between N+ source region 240 and gate oxide 110 (similar to the embodiment of Figure 9) and two N wells, 234 and 238, are then formed, respectively, beneath field oxide 44 and field oxide 230. N wells 234 and 238 are both formed contiguous and in electrical contact with N+ source region 240 to thereby increase the effective volume of N+ source region 240.

25 c. Description of the Process of Forming the Structure

As previously alluded to, one of the features of the invention is that the effective volume of one or more of the source, floating drain, and emitter regions can be extended by the provision of contiguous and electrically connected wells which can be formed without the use of extra

masks or extra processing steps. Turning now to Figures 12-16, the process steps used to form the ESD protection structure of the embodiment of Figure 7 will be illustrated.

First of all, as shown in Figure 12, the main N well 50 is formed by the conventional doping of P type substrate 40 with an N dopant, such as phosphorus or arsenic, at an energy level  
5 sufficient to obtain the desired depth of N well 50, but at a dosage level insufficient to form N+ doping. Conventionally, this would be carried out while masking the remainder of substrate 40, i.e., masking the regions where N well 50 would not be formed. However, in accordance with the invention, photoresist mask 180 is formed with openings 182, 184, 186, and 188 (instead of a single mask opening 188 for formation of main N well 50). Mask  
10 opening 182 corresponds to the location where individual N well 72 beneath N+ source region 70 is to be formed in substrate 40, while mask opening 184 corresponds to the location where individual N well 103 will be formed in substrate 40 beneath field oxide region 56, with mask portion 183 separating these two individual N wells.

Mask openings 186 and 188 are formed in mask 180 to provide for the formation of main N  
15 well 50 in substrate 40, with mask portion 185 separating mask opening 186 from mask opening 184. The reason for two mask openings, separated by narrow mask portion 187, is to permit the formation of shallower P well 82 in N well 50. Shallow P well 82 may be formed during the formation of N wells 82, 103 and main N well 50 simply by masking substrate 40, since substrate 40 is already P doped sufficiently to comprise a P well, so the  
20 purpose of mask portion 187 is merely to prevent the underlying P doped substrate to be N doped, thus resulting in the formation of P well 82. It should be noted, in this regard, that the length of mask portion 187 (distance between opening 186 and opening 188) may be varied to, in turn, regulate the length and depth of P well 82, i.e., the depth before the N doped substrate portion beneath mask opening 186 merges with the N doped substrate portion beneath  
25 mask opening 188 to form the single main N well 50 in substrate 40. Generally the length of mask portion 187 will usually be about  $\frac{1}{2}$  the length of mask portion 185.

After formation of N wells 72, 103, and main N well 50, as well as P well 82, mask 180 is removed, and all of the active area of substrate 40 is masked with a mask 190 having openings therein conforming to regions within the active area of substrate 40 where field oxide is to be



grown, in addition to field oxide 42 which surrounds the active area. Thus, as shown in Figure 13, field oxide portions 42, 44, 52, 54, and 56 are shown formed on and in substrate 40 in the openings in mask 190.

Then, as shown in Figure 14, field oxide mask 190 is removed and gate oxide 110 and gate electrode 120 are conventionally formed over the region of substrate 40 between N well 72 and N well 102. As shown in Figure 15, N+ source region 70, N+ floating drain regions 100 and 100', and N+ contact region 90 may then be implanted by forming an implant mask 200 over portions of substrate 40 (including portions of N well 50), leaving exposed only those portions where the N+ implantation is to be made. It should be noted that gate electrode 120 and the field oxide portions 42, 44, 52, 54, and 56 form a self-alignment mask for the respective formations of N+ source region 70, N+ floating drain regions 100 and 100', and N+ contact region 90.

Following formation of the N+ regions, mask 200 may be removed and replaced with a second implant mask 204, as shown in Figure 16, formed over the N+ implanted areas to permit formation of the P+ implants comprising P+ contact 60 and P+ emitter region 80.

It should be noted, in this regard, that the P+ and N+ implant steps may be reversed, as is well known to those skilled in the art. Furthermore, one of the implant masks, e.g., mask 200, could be eliminated by increasing the dosage of the N+ implant sufficiently so that the subsequent P+ implant does not sufficiently change the N+ doped regions to render their doping levels less than that of an N+ doped region.

Thus, it will be seen that the additional N wells 72 and 103, as well as the additional P well 82, are formed without any additional masking or processing steps needed, since, as shown in Figure 12, individual N wells 72 and 103, as well as individual P well 82, are all formed at the same time as main N well 50, and the mask used to form main N well 50 may be modified for use in the simultaneous formation of N wells 72 and 103 and P well 82, i.e., no additional mask need be used. Furthermore, the subsequent step of masking active regions of substrate 40 shown in Figure 13, is carried out regardless of the presence of the additional

individual N wells and P well, and the remaining steps illustrated in Figures 14-16 are also carried out regardless of the presence or absence of the additional individual wells.

Therefore, using the structure and process of the invention, the energy dissipation capacity of the disclosed SCR structure may be increased sufficiently to handle the energy or power from a 2 kV HBM zapping mode with a circuitry width of less than 2.5 mils ( $63.5\ \mu\text{m}$ ) with an average junction depth of  $0.2\ \mu\text{m}$  or less, to provide the required ESD protection for integrated circuit structures such as I/O buffer circuits without, however, adding further processing steps or additional masking steps to the process.

While the structure and process of the invention have been illustrated with respect to their use with the primary ESD protection structure for an integrated circuit structure, and particularly with respect to the I/O buffers, the structure and process of the invention may also be used in connection with the CMOS devices used as ESD diodes, as well as with the CMOS used for the buffer drivers for output buffers, to provide secondary ESD protection for the integrated circuit structure. Figure 17 shows, in diagram form, the relationship of I/O pad 242, the primary ESD protection structure comprising the SCR structure denoted at 244, the ESD resistor 246, and the output buffer and/or input receiver section 248 for the N drivers and P drivers which provides secondary ESD protection for the remainder of the integrated circuit structure electrically connected thereto.

Specific circuitry for the secondary ESD protection structure is shown in Figures 18 and 19. In Figure 18, an output driver structure 248a is illustrated wherein ESD resistor 246 is shown connected at node N6 to the common drain 250 of a CMOS structure, wherein a source 252 and a gate 254 of the NMOS portion of the CMOS structure are connected to ground, i.e., a Vss bus 260, while a source 256 and gate 258 of the PMOS portion of the CMOS structure is electrically connected to a power (Vdd) bus 264. N6 is further connected to a second CMOS structure in output buffer 248a by a line 268. The second CMOS structure in output buffer 248a comprises a common drain 270 connected to line 268, an NMOS source 272 connected to Vss ground bus 260, and an NMOS gate electrode 274 which is connected to the remainder of the integrated circuit structure. The second CMOS structure further comprises a PMOS source 276 connected to Vdd power bus 264 and a PMOS gate electrode 278 which

is also connected to the remainder of the integrated circuit structure. Each of these NMOS and PMOS source and drain regions in both of the CMOS structures may have their effective volumes increased, in accordance with the invention, to increase their effectiveness as ESD protective structures, by providing an individual well physically and electrically contacting the individual N+ or P+ source or drain region, as will be described further below.

Figure 19 shows an input receiver structure located between ESD resistor 246 and the remainder of the integrated circuit structure with the portion 248b encompassed by the dotted lines and comprising the ESD diode portion of the input receiver structure. In this structure ESD diode portion 248b provides the ESD protection. It will be recognized that ESD diode structure 248b is identical to the first CMOS structure of output buffer 248a of Figure 18 so the numerals in Figure 19 for the components of ESD diode 248b are identical to the numerals used in Figure 18 to describe the first CMOS structure. The second CMOS structure shown in Figure 19 does not form part of the ESD protection and therefore will not be further described herein.

Thus, the structure and process of the invention may be applied to the formation of the common first CMOS structure of both the output buffer structure of Figure 18 and the input receiver structure of Figure 19, as well as the second CMOS structure of Figure 18, to enhance the energy or power dissipation of all of the respective illustrated CMOS structures within the dotted lines to provide improved ESD protection to the integrated circuit structures associated therewith.

Referring now to Figure 20, the ESD diode structure 248b of the input receiver of Figure 19 is shown in cross-section along its length, with individual N wells and P wells shown formed below the respective P+ and N+ sources and drains in accordance with the invention. Thus, an individual N well 280 is shown formed below (and in contact with) N+ source region 256 of the PMOS device formed in P type substrate 290 and an N well 282 is shown formed below (and in contact with) drain region 250a of the PMOS device, while an individual P well 284 is shown formed below (and in contact with) P+ source region 252 of the NMOS device formed in main N well 292, and an individual P well 286 is shown below (and in contact with) P+ drain region 250b of the NMOS device. It will be noted here that common drain region

250 shown in Figure 18, i.e., the common drain for both the PMOS and NMOS devices comprising the CMOS structure, is illustrated as an N+ drain region 250a and a P+ drain region 250b, it being understood that drain regions 250a and 250b will be electrically connected together by a suitable polysilicon, metal silicide, or metal interconnect at a subsequent stage in the construction of the integrated circuit structure.

Figure 21 shows a preferred method of forming the structure shown in Figure 20 wherein no additional processing steps or masks are utilized. In this embodiment, the individual N wells 280 and 282 and P wells 284 and 286 for the respective N+ and P+ source and drain regions are formed simultaneously with the formation of main N well 292 for the PMOS device of the CMOS structure. This method, which is substantially the same as that previously illustrated in Figures 12 and 13, utilizes a common mask 300 for the simultaneous formation of all of the individual N wells and P wells, as well as main N well 292, in P doped substrate 290. As in the previously described method of Figures 12 and 13, it will be recognized that the method may also be used with an N doped substrate wherein all of the individual N wells and P wells, as well as the main P well, would then be formed simultaneously in the N doped substrate using a common mask.

It should be recognized that while Figures 18 and 19 respectively show an output buffer circuit and an input receiver, the two structures may be combined into a common structure and the invention will be accordingly applied to those portions of the common structure which provide the ESD protection. It should also be noted that whether designed as separate or combined circuits, the enhanced ESD protection provided by the invention for the output buffer/input receiver structure, i.e., the secondary ESD protection structure, may be sufficient to permit elimination of the primary ESD protection structure, i.e., SCR structure 244 and ESD resistor 246, which would result in yet a further savings in layout area used to provide the ESD-protected I/O structures of the integrated circuit structure.

It should also be noted that while the respective N wells and P wells have been illustrated as formed directly below the respective N+ and P+ source and drain regions, the respective N wells and P wells may be formed offset (but still touching) the respective N+ and P+ source

and drain regions, including under adjacent field oxide portions, as discussed and illustrated with respect to the previous embodiment having the SCR structure formed therein.

Having thus described the invention what is claimed is:

1. A method for improving the energy dissipation characteristics of devices used to protect portions of an integrated circuit structure from damage from electrostatic discharge (ESD) which comprises: forming one or more individual P or N wells in a semiconductor substrate contiguous with one or more P+ or N+ active regions of the same conductivity type formed  
5 in said semiconductor substrate to extend the effective volume of said one or more P+ or N+ active regions in said substrate.
2. The method of claim 1 wherein said devices used to protect said integrated circuit structure from ESD include one or more active regions selected from the group consisting of source, drain, or emitter regions.
3. The method of claim 2 wherein said step of forming one or more individual wells in a semiconductor substrate contiguous with one or more P+ or N+ active regions formed in said semiconductor substrate further comprises forming at least one individual P well in said substrate contiguous with at least one P+ active region to extend the effective volume of said  
5 P+ region to thereby enhance the energy dissipation capacity of said P+ active region.
4. The method of claim 3 wherein said at least one individual P well is formed in a main N well formed in a P doped semiconductor substrate.
5. The method of claim 2 wherein said step of forming one or more individual wells in a semiconductor substrate contiguous with one or more P+ or N+ active regions formed in said semiconductor substrate further comprises forming at least one individual N well in said substrate contiguous with at least one N+ active region to extend the effective volume of said  
5 N+ region to thereby enhance the energy dissipation capacity of said N+ active region.
6. The method of claim 5 wherein said at least one individual N well is formed in a main P well formed in an N doped semiconductor substrate.

7. The method of claim 1 wherein said devices used to protect said integrated circuit structure from ESD comprise one or more MOS devices and said one or more P+ or N+ active regions comprise source or drain regions of said one or more MOS devices.

8. The method of claim 1 wherein said devices used to protect said integrated circuit structure from ESD comprise one or more bipolar devices and said one or more P+ or N+ active regions comprise an emitter region of said one or more bipolar devices.

9. A method for improving the energy dissipation characteristics of devices used to protect portions of an integrated circuit structure from damage from electrostatic discharge (ESD) which comprises the steps of:

- 5           a) forming one or more individual P or N wells in a semiconductor substrate simultaneous with the formation of a main well in said semiconductor substrate; and
- b) forming one or more P+ or N+ active regions in said semiconductor substrate contiguous with one or more of said individual wells of the same conductivity type to thereby extent the effective volume of said one or more P+ or N+ active regions in said substrate.

10. The method of claim 9 wherein said one or more individual P or N wells are formed using the same mask used to form said one or more P or N main wells in said substrate, whereby no additional processing steps or masks need be used to form said individual wells.

11. The process of claim 10 wherein said one or more individual N wells are formed at the same time as said one or more main N wells and using the same mask used to form said one or more main N wells.

12. The process of claim 10 wherein said one or more individual P wells are formed at the same time as said one or more main P wells and using the same mask used to form said one or more main P wells.

13. The method of claim 10 wherein said one or more individual P or N wells are both formed at the same time and using the same mask used to form said one or more P or N main wells in said substrate by:

- a) providing a substrate doped to one conductivity type;
- 5      b) providing a doping mask having one or more openings therein through which one or more individual wells and one or more main wells of opposite conductivity to said one conductivity type may be formed in said substrate by blanket doping said masked substrate with dopant of opposite conductivity type to said one conductivity type, and masking off portions of said substrate less than the entire area of said substrate wherein
- 10      said one or more main wells of opposite conductivity type will be formed whereby one or more individual wells of said one conductivity type will be formed within the area of said substrate defined by said one or more of said main wells of opposite conductivity type during the subsequent doping of said substrate through said doping mask.

14. An improved article for protecting portions of an integrated circuit structure from damage from electrostatic discharge (ESD) comprising: an integrated circuit structure formed in said semiconductor substrate capable of dissipating energy from ESD comprising one or more P+ or N+ active regions with one or more individual P or N wells formed in said semiconductor

5      substrate contiguous with said one or more P+ or N+ active regions of the same conductivity type to thereby extent the effective volume of said one or more P+ or N+ active regions in said substrate to enhance the energy dissipating characteristics of said integrated circuit structure.

15. The improved article of claim 14 wherein said integrated circuit structure comprises an SCR structure having one or more P+ or N+ active source regions, one or more P+ or N+ active drain regions, and one or more P+ or N+ active emitter regions.

16. The improved article of claim 14 wherein said integrated circuit structure comprises a CMOS structure having one or more P+ or N+ active source regions and one or more P+ or N+ active drain regions.



17. Apparatus for protecting portions of an integrated circuit structure from damage from electrostatic discharge (ESD) comprising:

- a) a semiconductor substrate of a first conductivity type;
- b) a main well of a second conductivity type formed in said substrate;
- 5 c) a doped source region and a doped drain region of said second conductivity type formed in said substrate between a channel region in said substrate beneath a gate oxide and a gate electrode thereon, said drain region formed contiguous with said main well;
- d) a doped emitter region of said first conductivity type formed in said well of said second conductivity type, said doped emitter region separated from said doped drain
- 10 region by an isolation oxide region; and
- e) at least one individual well region formed deeper in said substrate than said doped source, drain, and emitter regions and contiguous with one of said doped source, drain, or emitter regions and of the same conductivity type, to extend the effective volume of said source, drain, or emitter regions to thereby enhance dissipation of energy
- 15 transmitted thereto by said ESD protection apparatus.

18. The ESD protection apparatus of claim 17 wherein said apparatus further comprises:

- a) a first doped contact region located in said substrate and formed of said first conductivity type to provide an electrical contact to said substrate, said first doped contact region spaced from said source region in said substrate by an isolation oxide
- 5 region;
- b) a second doped contact region located in said well and formed of said second conductivity type to provide an electrical contact to said well, said second doped contact region separated from both said emitter region in said well and said drain region adjacent said well by further isolation oxide regions;
- 10 c) a first electrically conductive member electrically connecting said first doped contact region, said source region, and said gate electrode to a ground; and
- d) a second electrically conductive member electrically connecting said second doped contact region and said emitter region to a portion of said integrated circuit structure to be protected against damage from ESD.

19. MOS apparatus for protecting portions of an integrated circuit structure from damage from electrostatic discharge (ESD) comprising:
- a) a semiconductor substrate of one conductivity type;
  - b) a first doped source region and a first doped drain region formed in said substrate between a channel region in said substrate beneath a gate oxide and a gate electrode thereon;
  - c) at least one individual well region formed deeper in said substrate than said first doped source and drain regions and contiguous with one of said first doped source or drain regions and of the same conductivity type, to extend the effective volume of said first doped source or drain regions to thereby enhance dissipation of energy transmitted thereto by said ESD protection apparatus.
20. The MOS apparatus for providing ESD protection of claim 19 wherein said apparatus further comprises:
- a) a main well of opposite conductivity type to said semiconductor substrate and containing second source and drain regions doped to an opposite conductivity type than said first doped source and drain regions in said substrate, said second source and drain regions formed between a channel region in said well beneath a gate oxide and a gate electrode thereon; and
  - b) at least one individual well region formed deeper in said main well than said second doped source and drain regions and contiguous with one of said second doped source or drain regions and of the same conductivity type, to extend the effective volume of said second doped source or drain regions to thereby enhance dissipation of energy transmitted thereto by said ESD protection apparatus.
21. The MOS apparatus for providing ESD protection of claim 20 wherein said main well and said individual wells are formed in the same step using the same mask.

22. The MOS apparatus for providing ESD protection of claim 20 wherein first and second drain regions are electrically connected together; one of said first and second source regions and said gate electrode adjacent thereto are connected to ground; and the other of said source regions and said gate electrode adjacent thereto are connected to a portion of said integrated
- 5 circuit structure to be protected from ESD.

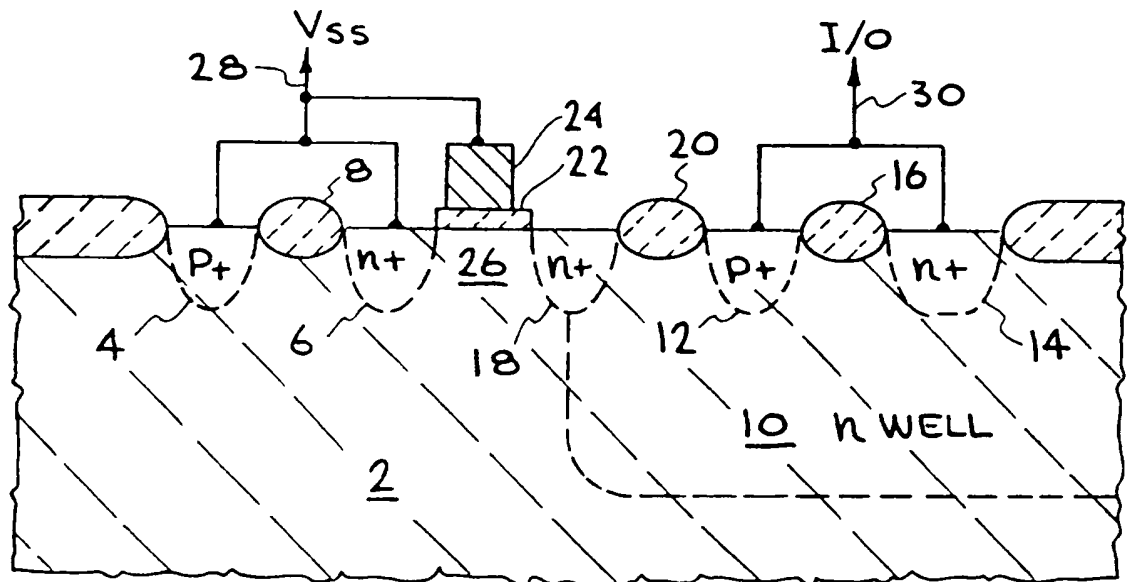


FIG. 1

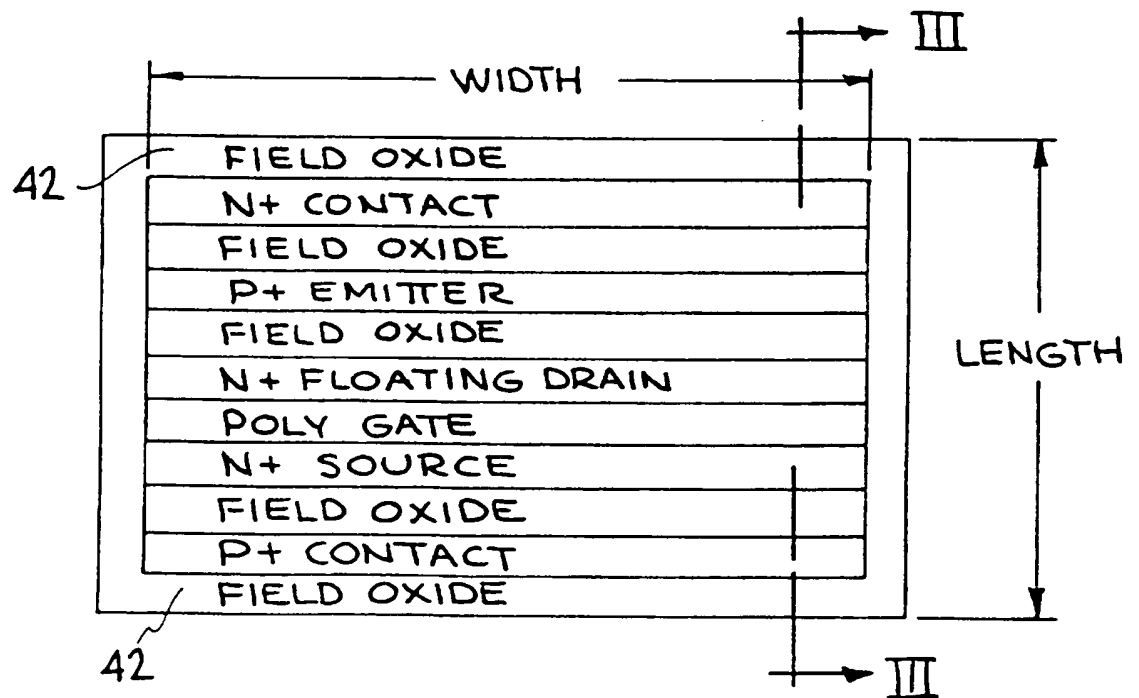
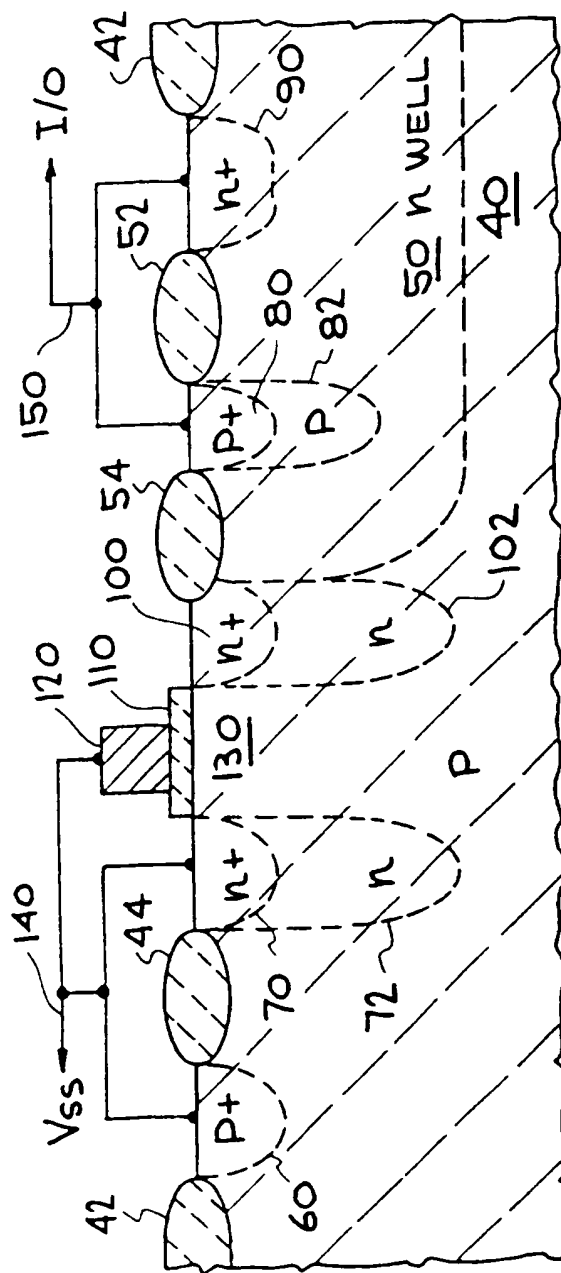
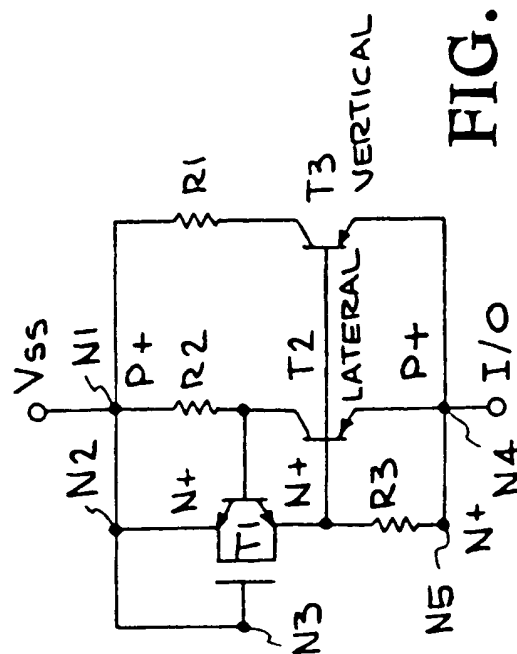


FIG. 2

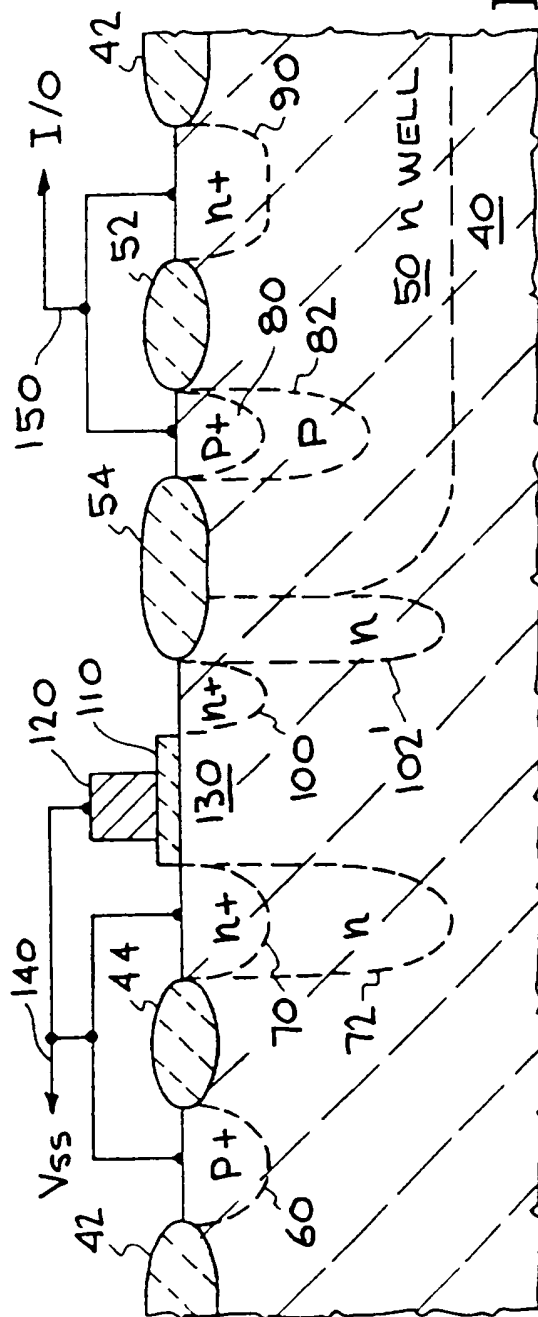


**FIG. 3**

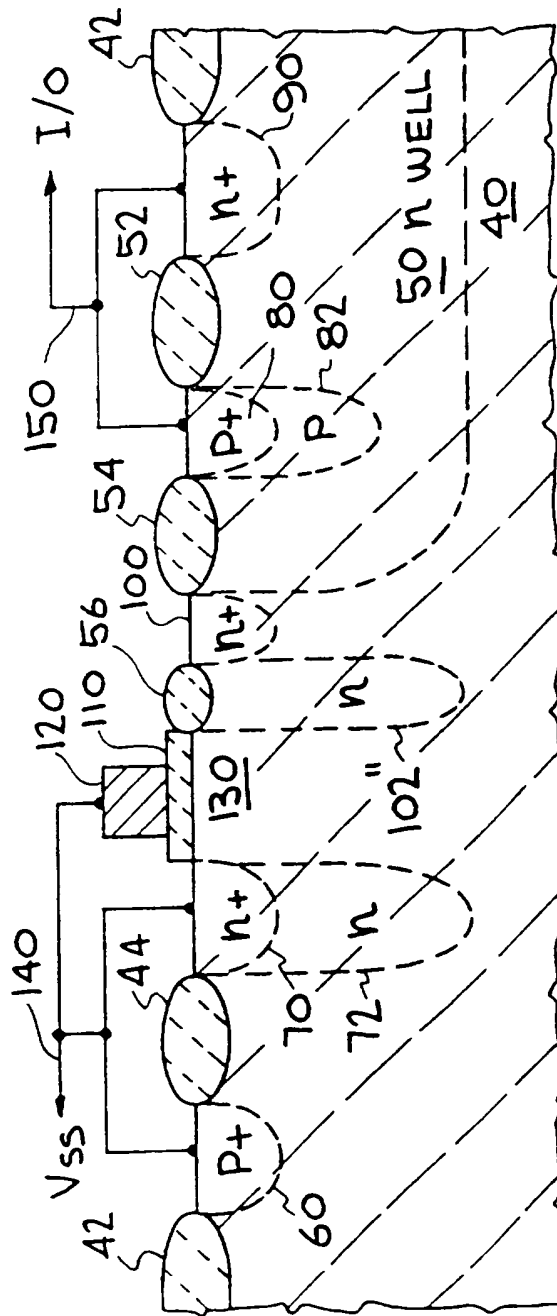


**FIG. 4**

**FIG. 5**



**FIG. 6**



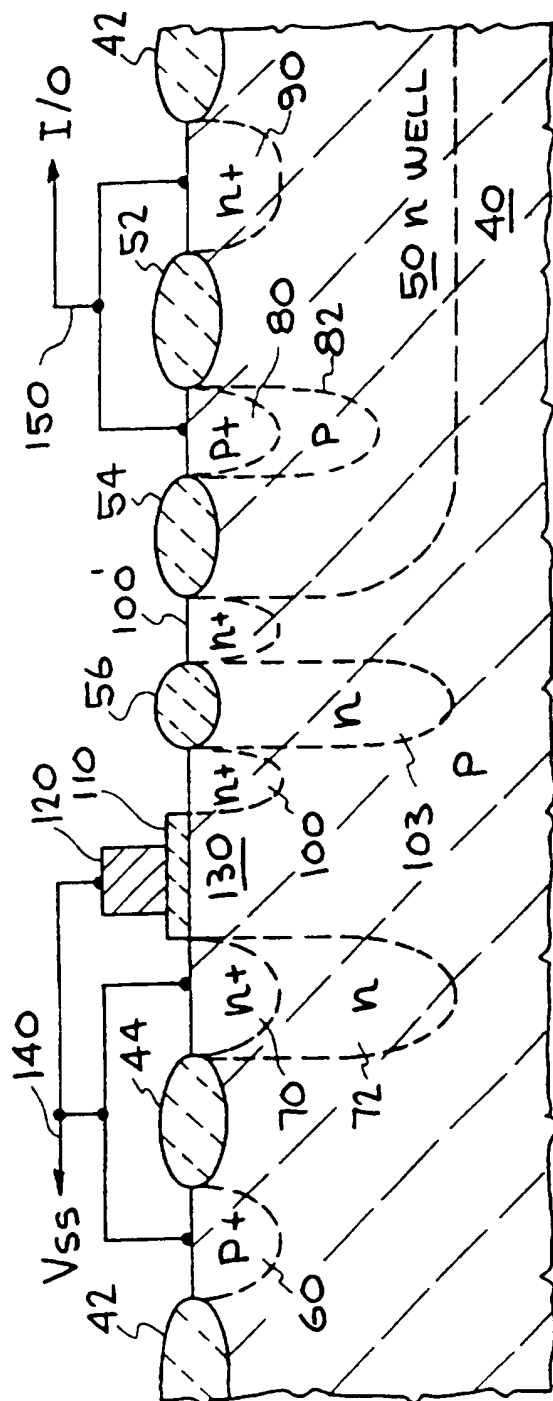


FIG. 7

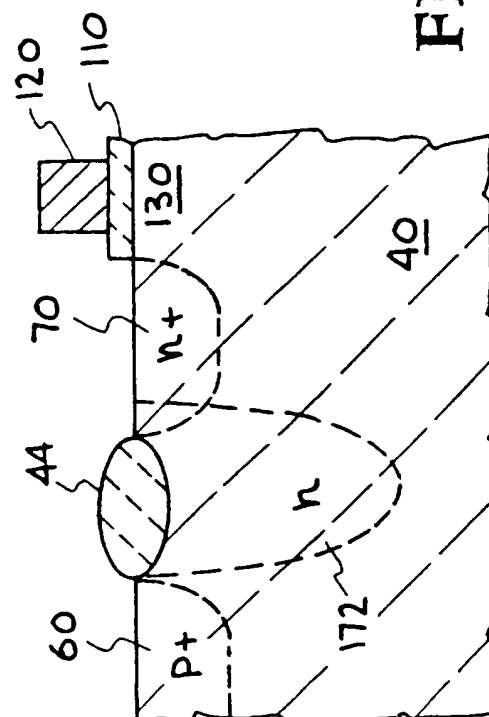


FIG. 8

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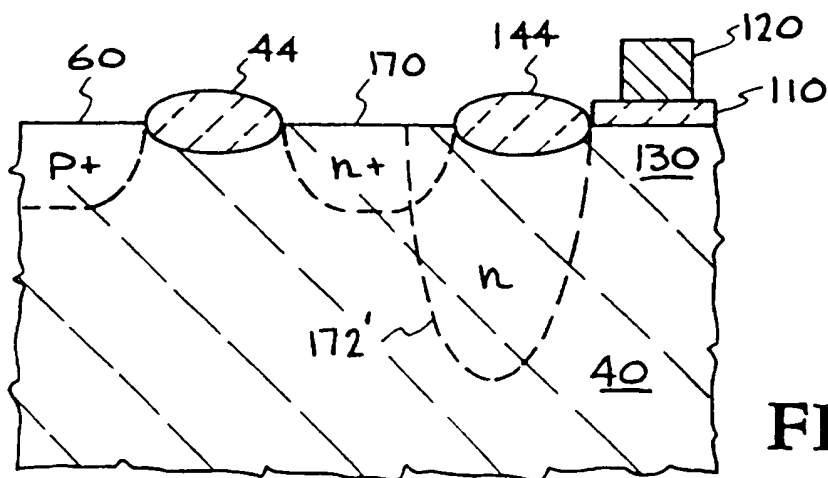


FIG. 9

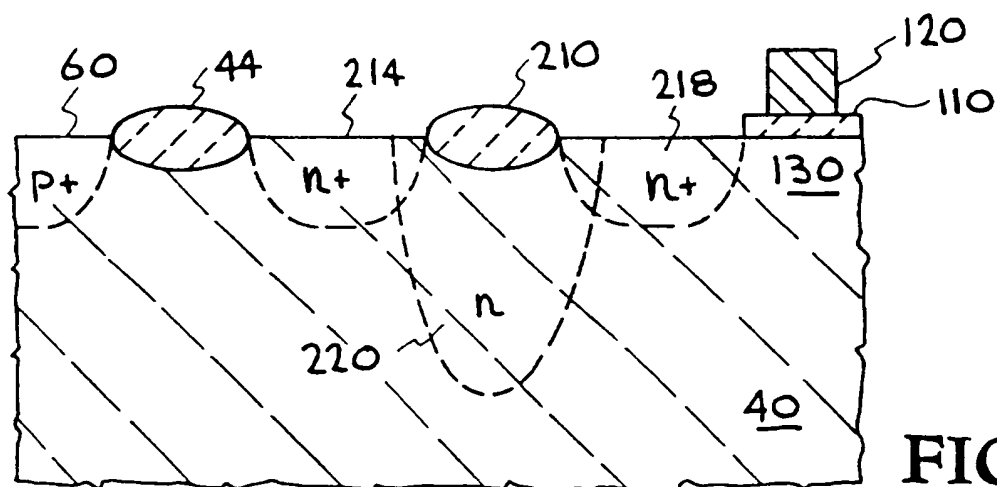


FIG. 10

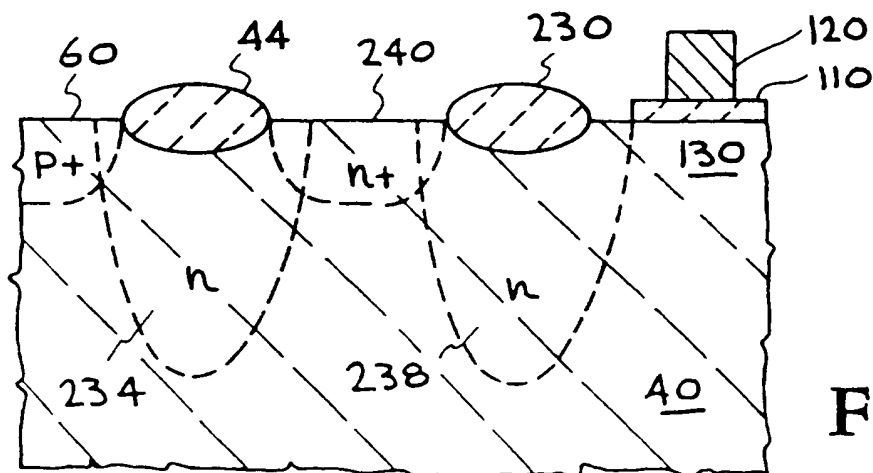


FIG. 11



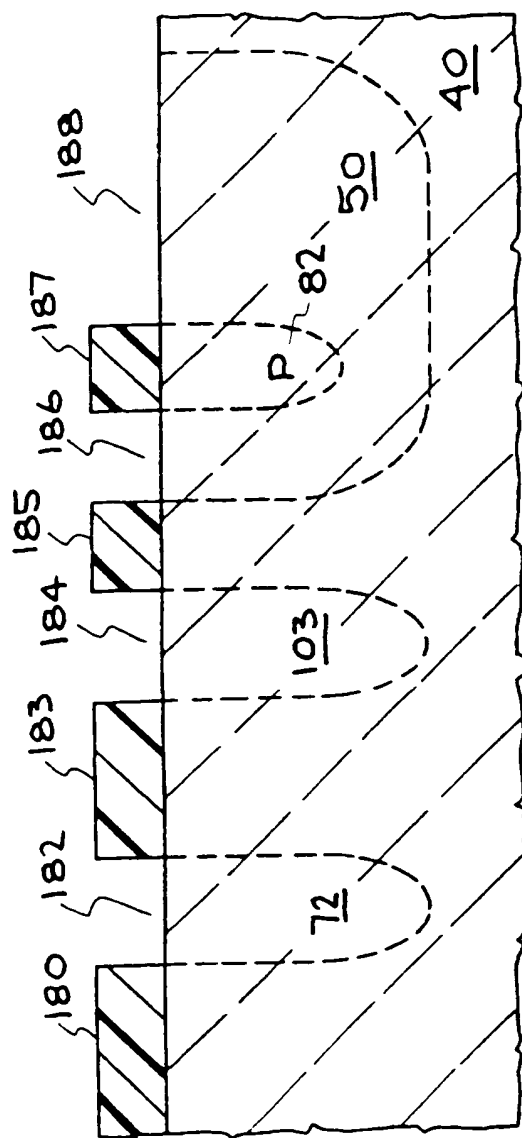


FIG. 12

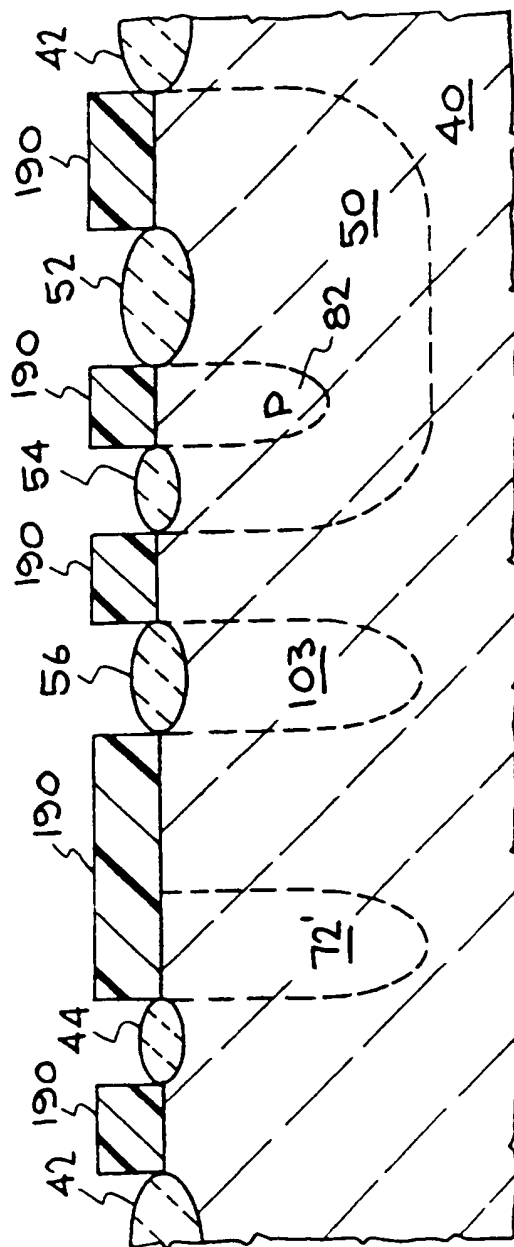
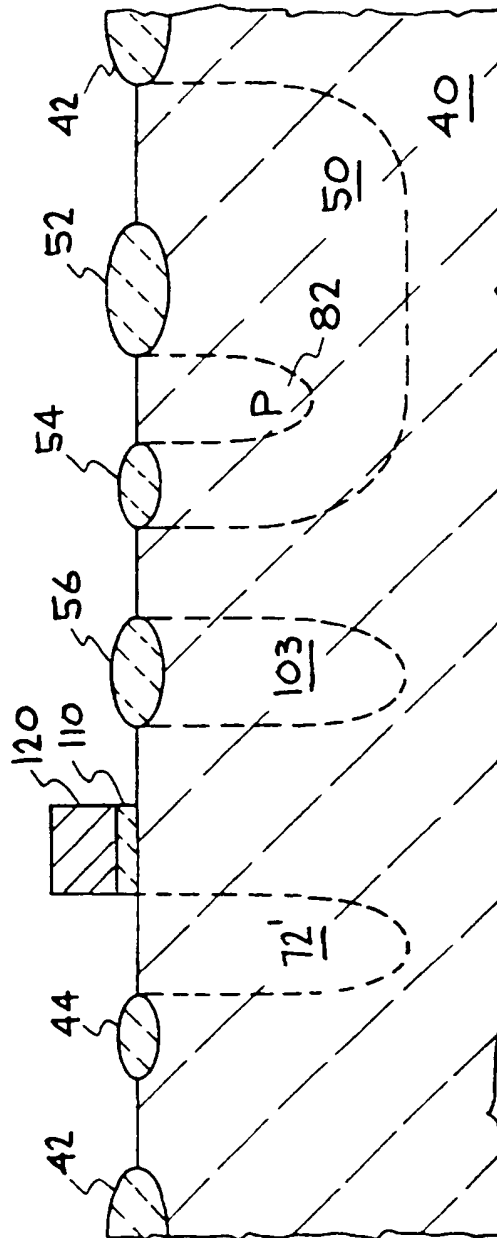
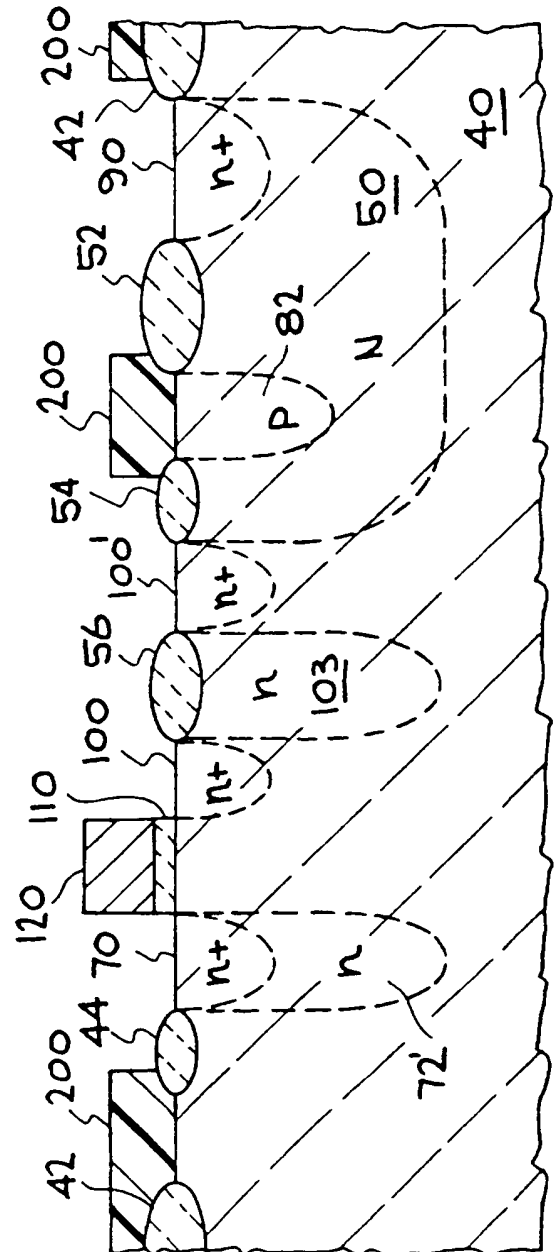


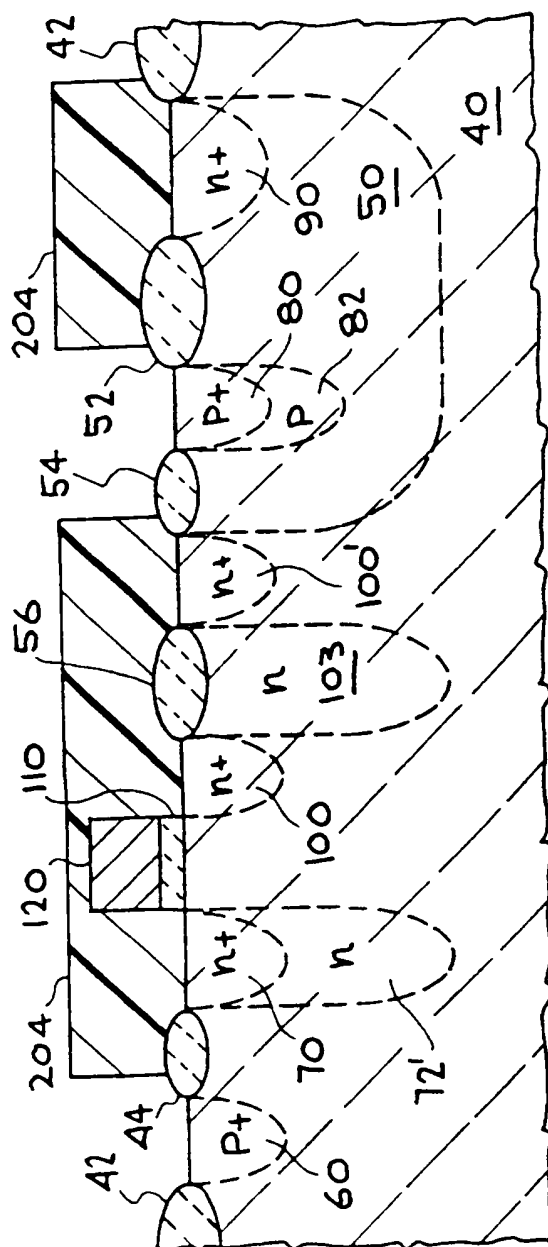
FIG. 13

**FIG. 14**



**FIG. 15**





**FIG. 16**

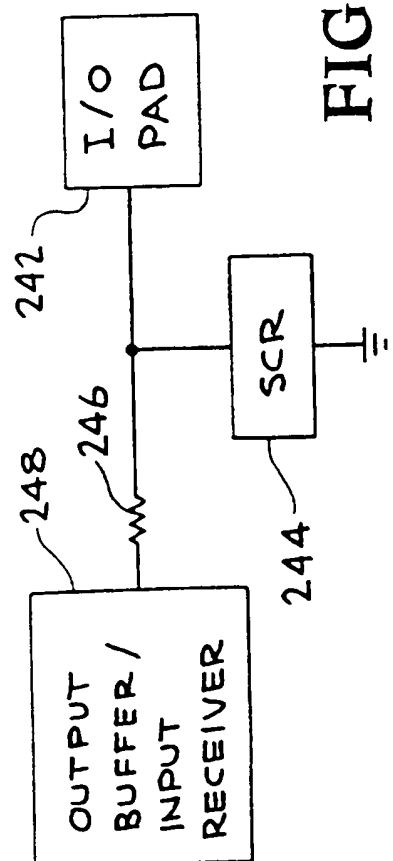


FIG. 17

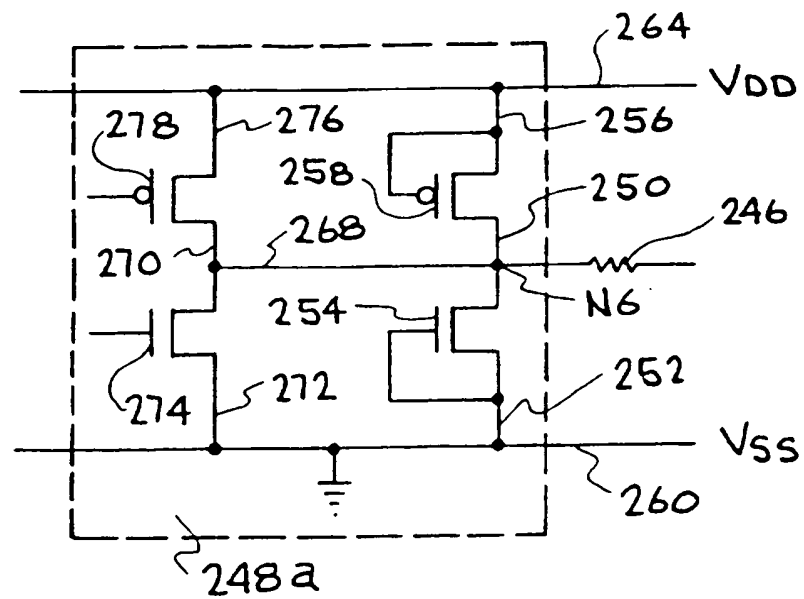


FIG. 18

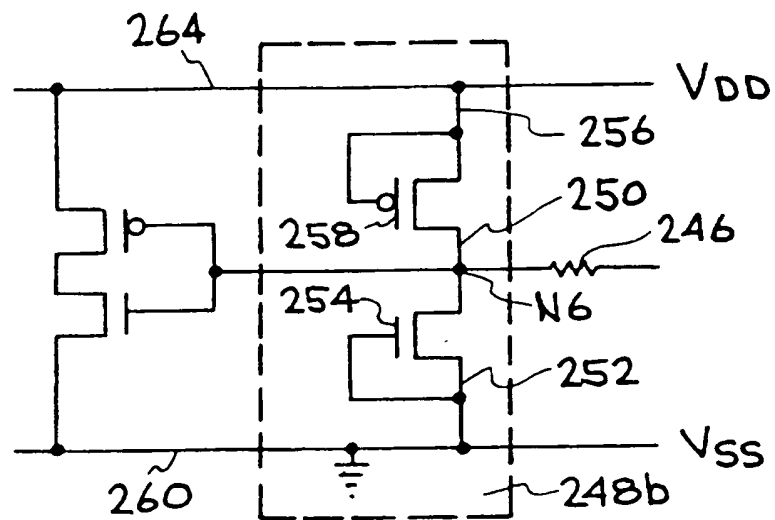


FIG. 19

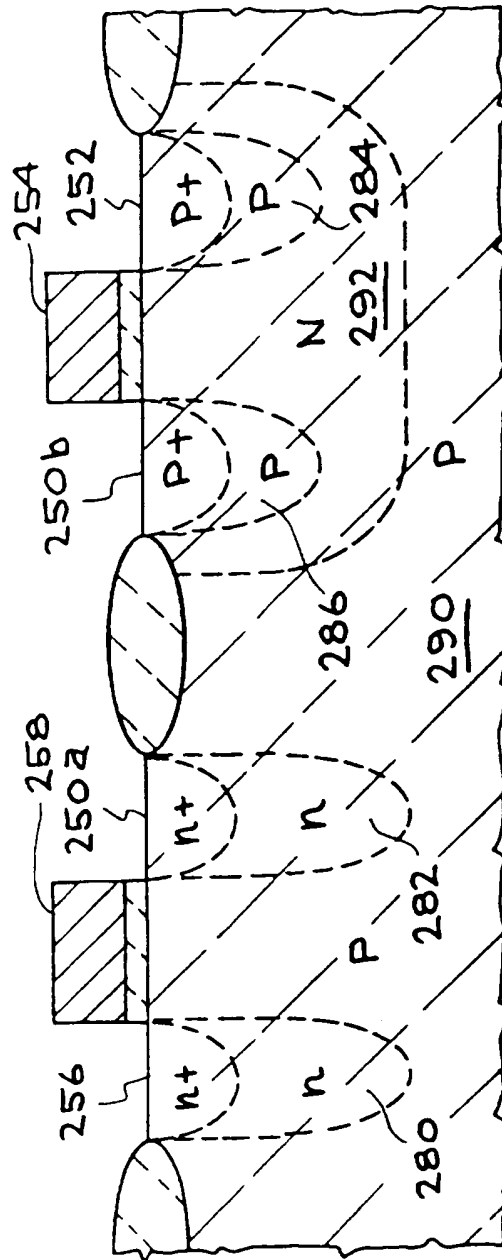


FIG. 20

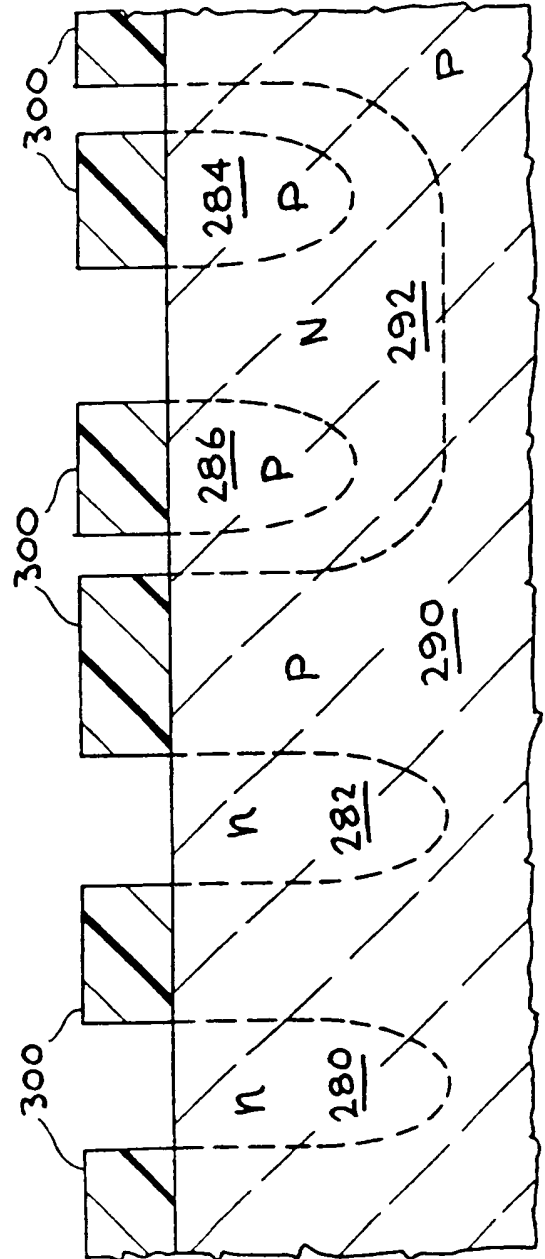


FIG. 21

# INTERNATIONAL SEARCH REPORT

International Application No

PCT/US 97/12603

**A. CLASSIFICATION OF SUBJECT MATTER**  
IPC 6 H01L27/02

According to International Patent Classification (IPC) or to both national classification and IPC

**B. FIELDS SEARCHED**

Minimum documentation searched (classification system followed by classification symbols)

IPC 6 H01L

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Electronic data base consulted during the international search (name of data base and, where practical, search terms used)

**C. DOCUMENTS CONSIDERED TO BE RELEVANT**

Category *	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
Y	AMITAVA CHATTERJEE ET AL: "A LOW-VOLTAGE TRIGGERING SCR FOR ON-CHIP ESD PROTECTION AT OUTPUT AND INPUT PADS" IEEE ELECTRON DEVICE LETTERS, vol. 12, no. 1, 1 January 1991, pages 21-22, XP000162296 see the whole document ---	1-22
Y	US 5 296 393 A (SMAYLING MICHAEL C ET AL) 22 March 1994 see column 12, line 42 - line 47 see column 14, line 22 - line 33 see column 18, line 26 - line 33 see column 45, line 16 - line 21 see figures 6B,6G --- -/--	1-22

☒ Further documents are listed in the continuation of box C

☒ Patent family members are listed in annex

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- \*P\* document published prior to the international filing date but later than the priority date claimed

\*T\* later document published after the international filing date or priority date and not in conflict with the application but cited to understand the principle or theory underlying the invention

\*X\* document of particular relevance; the claimed invention cannot be considered novel or cannot be considered to involve an inventive step when the document is taken alone

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Date of the actual completion of the international search

2 October 1997

Date of mailing of the international search report

25. 10. 97

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Authorized officer

Vendange, P

# INTERNATIONAL SEARCH REPORT

International Application No

PCT/US 97/12603

## C.(Continuation) DOCUMENTS CONSIDERED TO BE RELEVANT

Category *	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No
A	<p>EP 0 568 341 A (TEXAS INSTRUMENTS INC) 3  November 1993  see column 1, line 35 - line 42; figures  5-7</p> <p style="text-align: center;">-----</p>	1-22

1

# INTERNATIONAL SEARCH REPORT

Information on patent family members

International Application No

PCT/US 97/12603

Patent document cited in search report	Publication date	Patent family member(s)	Publication date
US 5296393 A	22-03-94	JP 6112416 A	22-04-94
EP 0568341 A	03-11-93	JP 6283673 A	07-10-94